



PRODUCT NAME : 2N4126 PNP General Purpose Transistor

PRICE : Rs 20.00

SKU : RM2058



NOTE: THE PRODUCT MAY BE DIFFERENT FROM IMAGE SHOWN. Copyrights by Robomart.com

DESCRIPTION

Features

- Collector-Emitter Volt (V_{ce0}): 25V
- Collector-Base Volt (V_{cb0}): 25V
- Collector Current (I_c): 0.3A
- h_{fe} : 120-360 @ 2mA
- Power Dissipation (P_{tot}): 500mW
- Current-Gain-Bandwidth (f_{total}): 250MHz
- Type: PNP

PNP general purpose transistor

2N4126

FEATURES

- Low current (max. 200 mA)
- Low voltage (max. 25 V).

APPLICATIONS

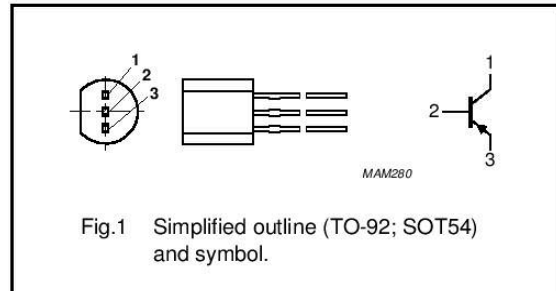
- General purpose switching and amplification, e.g. small-signal audio-frequency applications.

DESCRIPTION

PNP transistor in a TO-92; SOT54 plastic package. NPN complement: 2N4124.

PINNING

PIN	DESCRIPTION
1	collector
2	base
3	emitter



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–25	V
V_{CEO}	collector-emitter voltage	open base	–	–25	V
I_{CM}	peak collector current		–	–300	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	–	500	mW
h_{FE}	DC current gain	$I_C = -2\text{ mA}; V_{CE} = -1\text{ V}$	120	360	
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -20\text{ V}; f = 100\text{ MHz}$	250	–	MHz

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–25	V
V_{CEO}	collector-emitter voltage	open base	–	–25	V
V_{EBO}	emitter-base voltage	open collector	–	–4	V
I_C	collector current (DC)		–	–200	mA
I_{CM}	peak collector current		–	–300	mA
I_{BM}	peak base current		–	–100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	500	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	250	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = -20\text{ V}$	–	–50	nA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = -3\text{ V}$	–	–50	nA
h_{FE}	DC current gain	$I_C = -2\text{ mA}$; $V_{CE} = -1\text{ V}$; note 1	120	360	
		$I_C = -50\text{ mA}$; $V_{CE} = -1\text{ V}$; note 1	60	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -50\text{ mA}$; $I_B = -5\text{ mA}$; note 1	–	–400	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -50\text{ mA}$; $I_B = -5\text{ mA}$; note 1	–	–950	mV
C_c	collector capacitance	$I_E = I_E = 0$; $V_{CB} = -5\text{ V}$; $f = 1\text{ MHz}$	–	4.5	pF
C_e	emitter capacitance	$I_C = I_C = 0$; $V_{EB} = -0.5\text{ V}$; $f = 1\text{ MHz}$	–	10	pF
f_T	transition frequency	$I_C = -10\text{ mA}$; $V_{CE} = -20\text{ V}$; $f = 100\text{ MHz}$	250	–	MHz
F	noise figure	$I_C = -100\text{ }\mu\text{A}$; $V_{CE} = -5\text{ V}$; $R_S = 1\text{ k}\Omega$; $f = 10\text{ Hz to }15.7\text{ kHz}$	–	4	dB

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

